CLAIMS

1. A sputtering target for a magnetic recording medium, comprising: a metal phase containing Pt and at least one or more selected from Mn and V, with the balance being Co and incidental impurities; and an oxide phase which contains at least B and O and does not contain Mg and Al.

2. The sputtering target for a magnetic recording medium according to Claim 1, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt and 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

3. A sputtering target for a magnetic recording medium, comprising: a metal phase containing Pt, at least one or more selected from Mn and V, and Ru, with the balance being Co and incidental impurities; and an oxide phase which contains at least B and O and does not contain Mg and Al.

4. The sputtering target for a magnetic recording medium according to Claim 3, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt, 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, and more than 0.5 mol% and 30 mol% or less of Ru; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

5. The sputtering target for a magnetic recording medium according to any one of Claims 1 to 4, wherein the oxide phase further contains an oxide of at least one element selected from V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr.

6. A sputtering target for a magnetic recording medium, comprising: a metal phase containing Pt and at least one or more selected from Mn and V, with the balance being Co and

incidental impurities; and an oxide phase which does not contain Mg and Al.

7. The sputtering target for a magnetic recording medium according to Claim 6, containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt and 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

8. A sputtering target for a magnetic recording medium, comprising: a metal phase containing Pt, at least one or more selected from Mn and V, and Ru, with the balance being Co and incidental impurities; and an oxide phase which does not contain Mg and Al.

9. The sputtering target for a magnetic recording medium according to Claim 8~~7~~,

containing, based on total metal phase components of the sputtering target for a magnetic recording medium, 1 mol% or more and 30 mol% or less of Pt, 0.5 mol% or more and 10 mol% or less of at least one or more selected from Mn and V, and more than 0.5 mol% and 30 mol% or less of Ru; and

comprising, based on the sputtering target for a magnetic recording medium as a whole, 25 vol% or more and 40 vol% or less of the oxide phase.

10. The sputtering target for a magnetic recording medium according to any one of Claims 6 to 9, wherein the oxide phase further contains an oxide of at least one element selected from B, V, Ru, Ti, Si, Ta, Cr, Nb, Mn, Co, Ni, Zn, Y, Mo, W, La, Ce, Nd, Sm, Eu, Gd, Yb, Lu, and Zr.